BZX84BxxxLT1G, BZX84CxxxLT1G Series, SZBZX84BxxxLT1G, SZBZX84CxxxLT1G Series

Zener Voltage Regulators

225 mW SOT-23 Surface Mount

This series of Zener diodes is offered in the convenient, surface mount plastic SOT-23 package. These devices are designed to provide voltage regulation with minimum space requirement. They are well suited for applications such as cellular phones, hand held portables, and high density PC boards.

Features

- 225 mW Rating on FR-4 or FR-5 Board
- Zener Breakdown Voltage Range 2.4 V to 75 V
- Package Designed for Optimal Automated Board Assembly
- Small Package Size for High Density Applications
- ESD Rating of Class 3 (> 16 kV) per Human Body Model
- Tight Tolerance Series Available (See Page 4)
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

Mechanical Characteristics

CASE: Void-free, transfer-molded, thermosetting plastic case **FINISH:** Corrosion resistant finish, easily Solderable **MAXIMUM CASE TEMPERATURE FOR SOLDERING PURPOSES:** 260°C for 10 Seconds

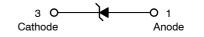
POLARITY: Cathode indicated by polarity band **FLAMMABILITY RATING:** UL 94 V–0



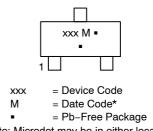
ON Semiconductor®

http://onsemi.com





MARKING DIAGRAM



(Note: Microdot may be in either location) *Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
BZX84CxxxLT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SZBZX84CxxxLT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
BZX84CxxxLT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SZBZX84CxxxLT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
BZX84BxxxLT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SZBZX84BxxxLT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
BZX84BxxxLT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

+ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

DEVICE MARKING INFORMATION

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

See specific marking information in the device marking column of the Electrical Characteristics table on page 3 of this data sheet.

BZX84BxxxLT1G, BZX84CxxxLT1G Series, SZBZX84BxxxLT1G, SZBZX84CxxxLT1G Series

MAXIMUM RATINGS

Rating	Symbol	Мах	Unit
Total Power Dissipation on FR–5 Board,	PD	005	
(Note 1) @ $T_A = 25^{\circ}C$		225	mW
Derated above 25°C		1.8	mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{ heta JA}$	556	°C/W
Total Power Dissipation on Alumina	PD		
Substrate, (Note 2) @ T _A = 25°C		300	mW
Derated above 25°C		2.4	mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{ hetaJA}$	417	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-65 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

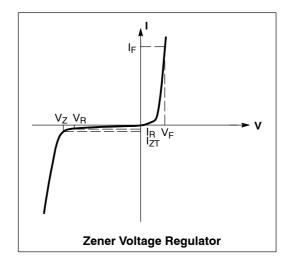
1. FR-5 = 1.0 X 0.75 X 0.62 in.

2. Alumina = 0.4 X 0.3 X 0.024 in., 99.5% alumina.

ELECTRICAL CHARACTERISTICS

(Pinout: 1-Anode, 2-No Connection, 3-Cathode) ($T_A = 25^{\circ}C$ unless otherwise noted, $V_F = 0.90$ V Max. @ $I_F = 10$ mA)

Symbol	Parameter
VZ	Reverse Zener Voltage @ I _{ZT}
I _{ZT}	Reverse Current
Z _{ZT}	Maximum Zener Impedance @ IZT
I _R	Reverse Leakage Current @ V _R
V _R	Reverse Voltage
١ _F	Forward Current
V _F	Forward Voltage @ I _F
ΘV _Z	Maximum Temperature Coefficient of Vz
С	Max. Capacitance @ $V_R = 0$ and f = 1 MHz



BZX84BxxxLT1G, BZX84CxxxLT1G Series, SZBZX84BxxxLT1G, SZBZX84CxxxLT1G Series

ELECTRICAL CHARACTERISTICS - BZX84CxxxLT1 SERIES (STANDARD TOLERANCE)

(Pinout: 1-Anode, 2-No Connection, 3-Cathode) ($T_A = 25^{\circ}C$ unless otherwise noted, $V_F = 0.90$ V Max. @ $I_F = 10$ mA) (Devices listed in **bold**, *italic* are ON Semiconductor Preferred devices.)

			V _{Z1} (Volts I _{ZT1} = 5 (Note 3)	mA	Z _{ZT1} (Ω)	@ I _{ZT2}	e (V) = 1 mA te 3)	Z _{ZT2} (Ω)		: (V) = 20 mA te 3)	Z _{ZT3} (Ω)	Leal	everse kage rent		/z //k) = 5 mA	C (pF)
Device*	Device Marking	Min	Nom	Max	@ I _{ZT1} = 5 mA	Min	Max	@ I _{ZT2} = 1 mA	Min	Max	@ I _{ZT3} = 20 mA	Ι _R μΑ @	V _R Volts	Min	Max	@ V _R = 0 f = 1 MHz
BZX84C2V4LT1G	Z11	2.2	2.4	2.6	100	1.7	2.1	600	2.6	3.2	50	50	1	-3.5	0	450
BZX84C2V7LT1G	Z12	2.5	2.7	2.9	100	1.9	2.4	600	3	3.6	50	20	1	-3.5	0	450
BZX84C3V0LT1G	Z13	2.8	3	3.2	95	2.1	2.7	600	3.3	3.9	50	10	1	-3.5	0	450
BZX84C3V3LT1G	Z14	3.1	3.3	3.5	95	2.3	2.9	600	3.6	4.2	40	5	1	-3.5	0	450
BZX84C3V6LT1G	Z15	3.4	3.6	3.8	90	2.7	3.3	600	3.9	4.5	40	5	1	-3.5	0	450
BZX84C3V9LT1G	Z16	3.7	3.9	4.1	90	2.9	3.5	600	4.1	4.7	30	3	1	-3.5	-2.5	450
BZX84C4V3LT1G	W9	4	4.3	4.6	90	3.3	4	600	4.4	5.1	30	3	1	-3.5	0	450
BZX84C4V7LT1/T3G	Z1	4.4	4.7	5	80	3.7	4.7	500	4.5	5.4	15	3	2	-3.5	0.2	260
BZX84C5V1LT1/T3G	Z2	4.8	5.1	5.4	60	4.2	5.3	480	5	5.9	15	2	2	-2.7	1.2	225
BZX84C5V6LT1/T3G	Z3	5.2	5.6	6	40	4.8	6	400	5.2	6.3	10	1	2	-2.0	2.5	200
BZX84C6V2LT1/T3G	Z4	5.8	6.2	6.6	10	5.6	6.6	150	5.8	6.8	6	3	4	0.4	3.7	185
BZX84C6V8LT1/T3G	Z5	6.4	6.8	7.2	15	6.3	7.2	80	6.4	7.4	6	2	4	1.2	4.5	155
BZX84C7V5LT1G	Z6	7	7.5	7.9	15	6.9	7.9	80	7	8	6	1	5	2.5	5.3	140
BZX84C8V2LT1G	Z7	7.7	8.2	8.7	15	7.6	8.7	80	7.7	8.8	6	0.7	5	3.2	6.2	135
BZX84C9V1LT1/T3G	Z8	8.5	9.1	9.6	15	8.4	9.6	100	8.5	9.7	8	0.5	6	3.8	7.0	130
BZX84C10LT1G	Z9	9.4	10	10.6	20	9.3	10.6	150	9.4	10.7	10	0.2	7	4.5	8.0	130
BZX84C11LT1G	Y1	10.4	11	11.6	20	10.2	11.6	150	10.4	11.8	10	0.1	8	5.4	9.0	130
BZX84C12LT1G	Y2	11.4	12	12.7	25	11.2	12.7	150	11.4	12.9	10	0.1	8	6.0	10.0	130
BZX84C13LT1G	Y3	12.4	13	14.1	30	12.3	14	170	12.5	14.2	15	0.1	8	7.0	11.0	120
BZX84C15LT1/T3G	Y4	13.8	15	15.6	30	13.7	15.5	200	13.9	15.7	20	0.05	10.5	9.2	13.0	110
BZX84C16LT1G	Y5	15.3	16	17.1	40	15.2	17	200	15.4	17.2	20	0.05	11.2	10.4	14.0	105
BZX84C18LT1/T3G	Y6	16.8	18	19.1	45	16.7	19	225	16.9	19.2	20	0.05	12.6	12.4	16.0	100
BZX84C20LT1G	Y7	18.8	20	21.2	55	18.7	21.1	225	18.9	21.4	20	0.05	14	14.4	18.0	85
BZX84C22LT1G	Y8	20.8	22	23.3	55	20.7	23.2	250	20.9	23.4	25	0.05	15.4	16.4	20.0	85
BZX84C24LT1G	Y9	22.8	24	25.6	70	22.7	25.5	250	22.9	25.7	25	0.05	16.8	18.4	22.0	80
			V _{Z1} Belo I _{ZT1} = 2		Z _{ZT1} Below	@ I _{ZT2}	3elow = 0.1 m- A	Z _{ZT2} Below	V _{Z3} E @ I _{ZT3} =		Z _{ZT3} Below	Leal	everse kage rent	se θ _{VZ} (mV/k) Below @ I _{ZT1} = 2 mA		C (pF)
Device*	Device Marking	Min	Nom	Max	@ I _{ZT1} = 2 mA	Min	Max	@ I _{ZT4} = 0.5 mA	Min	Max	@ I _{ZT3} = 10 mA	Ι _R μΑ @	₽ V _R ₽ (V)	Min	Max	@ V _R = 0 f = 1 MHz
BZX84C27LT1G	Y10	25.1	27	28.9	80	25	28.9	300	25.2	29.3	45	0.05	18.9	21.4	25.3	70
BZX84C30LT1G	Y11	28	30	32	80	27.8	32	300	28.1	32.4	50	0.05	21	24.4	29.4	70
BZX84C33LT1/T3G	Y12	31	33	35	80	30.8	35	325	31.1	35.4	55	0.05	23.1	27.4	33.4	70
BZX84C36LT1G	Y13	34	36	38	90	33.8	38	350	34.1	38.4	60	0.05	25.2	30.4	37.4	70
BZX84C39LT1G	Y14	37	39	41	130	36.7	41	350	37.1	41.5	70	0.05	27.3	33.4	41.2	45
BZX84C43LT1G	Y15	40	43	46	150	39.7	46	375	40.1	46.5	80	0.05	30.1	37.6	46.6	40
BZX84C47LT1G	Y16	44	47	50	170	43.7	50	375	44.1	50.5	90	0.05	32.9	42.0	51.8	40
BZX84C51LT1G	Y17	48	51	54	180	47.6	54	400	48.1	54.6	100	0.05	35.7	46.6	57.2	40
BZX84C56LT1G	Y18	52	56	60	200	51.5	60	425	52.1	60.8	110	0.05	39.2	52.2	63.8	40
BZX84C62LT1G	Y19	58	62	66	215	57.4	66	450	58.2	67	120	0.05	43.4	58.8	71.6	35
BZX84C68LT1G	Y20	64	68	72	240	63.4	72	475	64.2	73.2	130	0.05	47.6	65.6	79.8	35
																1

3. Zener voltage is measured with a pulse test current I_Z at an ambient temperature of 25°C.

*Include SZ-prefix devices where applicable.

BZX84BxxxLT1G, BZX84CxxxLT1G Series, SZBZX84BxxxLT1G, SZBZX84CxxxLT1G Series

ELECTRICAL CHARACTERISTICS – BZX84BxxxL (Tight Tolerance Series)

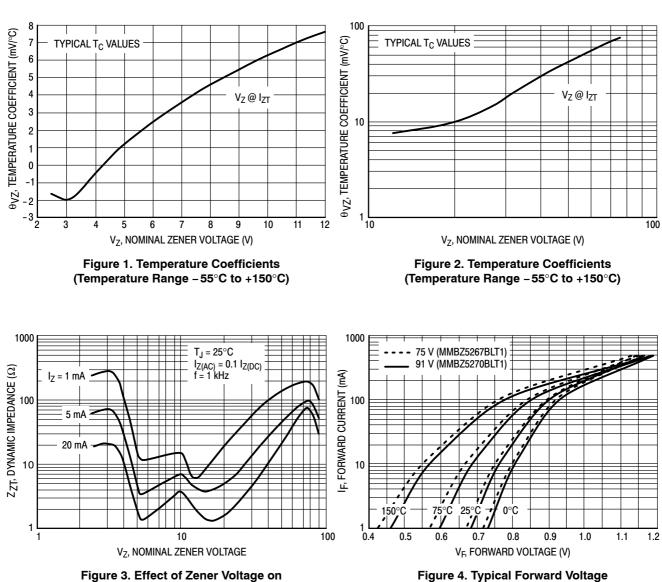
(Pinout: 1-Anode, 2-No Connection, 3-Cathode) (T_A = 25°C unless otherwise noted, V_F = 0.90 V Max. @ I_F = 10 mA)

		V7 (V0	lts) @ I _{ZT}	= 5 mA	Z _{ZT} (Ω) @ I _{ZT} = 5 mA	Max Rev Leaka Curre	ge	^θ ∨z (mV/k)		
	Device	2.	(Note 4)		(Note 4)	I _R @	VR	@ I _{ZT} = 5 mA		C (pF) @ V _B =0,
Device*	Marking	Min	Nom	Мах	Max	μA	Volts	Min	Max	f = 1 MHz
BZX84B4V7LT1G	T10	4.61	4.7	4.79	80	3	2	-3.5	0.2	260
BZX84B5V1LT1G	T11	5.00	5.1	5.20	60	2	2	-2.7	1.2	225
BZX84B5V6LT1G	T12	5.49	5.6	5.71	40	1	2	-2	2.5	200
BZX84B6V2LT1G	T13	6.08	6.2	6.32	10	3	4	0.4	3.7	185
BZX84B6V8LT1G	T14	6.66	6.8	6.94	15	2	4	1.2	4.5	155
BZX84B7V5LT1G	T15	7.35	7.5	7.65	15	1	5	2.5	5.3	140
BZX84B8V2LT1G	T16	8.04	8.2	8.36	15	0.7	5	3.2	6.2	135
BZX84B9V1LT1G	T17	8.92	9.1	9.28	15	0.5	6	3.8	7	130
BZX84B12LT1G	T18	11.8	12	12.2	25	0.1	8	6	10	130
BZX84B15LT1G	T22	14.7	15	15.3	30	0.05	10.5	9.2	13	110
BZX84B16LT1G	T19	15.7	16	16.3	40	0.05	11.2	10.4	14	105
BZX84B18LT1G	T20	17.6	18	18.4	45	0.05	12.6	12.4	16	100
BZX84B22LT1G	T24	21.6	22	22.4	55	0.05	15.4	16.4	20	85
BZX84B24LT1G	T25	23.5	24	24.5	70	0.05	16.8	18.4	22	80

4. Zener voltage is measured with a pulse test current I_Z at an ambient temperature of 25°C.

*Include SZ-prefix devices where applicable.

BZX84BxxxLT1G, BZX84CxxxLT1G Series, SZBZX84BxxxLT1G, SZBZX84CxxxLT1G Series TYPICAL CHARACTERISTICS



Zener Impedance

BZX84BxxxLT1G, BZX84CxxxLT1G Series, SZBZX84BxxxLT1G, SZBZX84CxxxLT1G Series TYPICAL CHARACTERISTICS

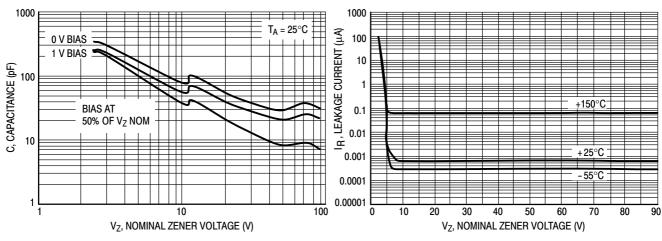


Figure 5. Typical Capacitance

Figure 6. Typical Leakage Current

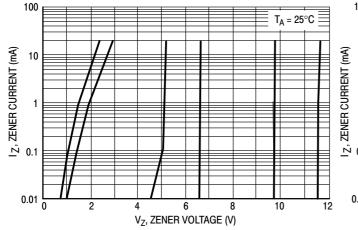


Figure 7. Zener Voltage versus Zener Current (V_Z Up to 12 V)

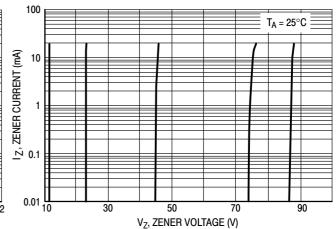
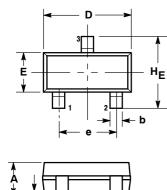
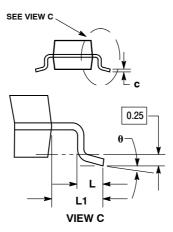


Figure 8. Zener Voltage versus Zener Current (12 V to 91 V)

BZX84BxxxLT1G, BZX84CxxxLT1G Series, SZBZX84BxxxLT1G, SZBZX84CxxxLT1G Series PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AP**





NOTES

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
- 3 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS, MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. 4

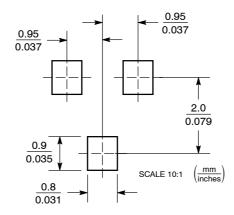
	м	ILLIMETE	RS	INCHES					
DIM	MIN	NOM	MAX	MIN	NOM	MAX			
Α	0.89	1.00	1.11	0.035	0.040	0.044			
A1	0.01	0.06	0.10	0.001	0.002	0.004			
b	0.37	0.44	0.50	0.015	0.018	0.020			
c	0.09	0.13	0.18	0.003	0.005	0.007			
D	2.80	2.90	3.04	0.110	0.114	0.120			
Е	1.20	1.30	1.40	0.047	0.051	0.055			
e	1.78	1.90	2.04	0.070	0.075	0.081			
L	0.10	0.20	0.30	0.004	0.008	0.012			
L1	0.35	0.54	0.69	0.014	0.021	0.029			
HE	2.10	2.40	2.64	0.083	0.094	0.104			
θ	0°		10°	0°		10°			

STYLE 8:

PIN 1. ANODE NO CONNECTION 2.

З. CATHODE

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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